

CD4093B Types

CMOS

Quad 2-Input NAND Schmitt Triggers

High-Voltage Types (20 Volt Rating)

The RCA-CD4093B consists of four Schmitt-trigger circuits. Each circuit functions as a two-input NAND gate with Schmitt-trigger action on both inputs. The gate switches at different points for positive- and negative-going signals. The difference between the positive voltage (V_P) and the negative voltage (V_N) is defined as hysteresis voltage (V_H) (see Fig. 2).

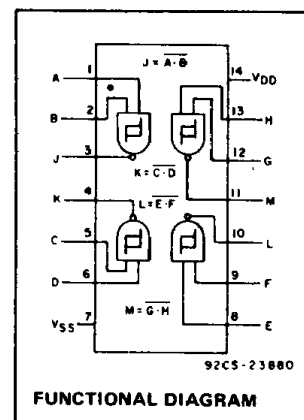
The CD4093B types are supplied in 14-lead hermetic dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic package (E suffix), 14-lead ceramic flat package (K suffix), and in chip form (H suffix).

Features:

- Schmitt-trigger action on each input with no external components
- Hysteresis voltage typically 0.9 V at $V_{DD} = 5$ V and 2.3 V at $V_{DD} = 10$ V
- Noise immunity greater than 50%
- No limit on input rise and fall times
- Standardized, symmetrical output characteristics
- 100% tested for quiescent current at 20 V
- Maximum input current of 1 μ A at 18 V over full package-temperature range, 100 nA at 18 V and 25°C
- 5-V, 10-V, and 15-V parametric ratings
- Meets all requirements of JEDEC Tentative Standard No. 13A, "Standard Specifications for Description of 'B' Series CMOS Devices"

Applications:

- Wave and pulse shapers
- High-noise-environment systems
- Monostable multivibrators
- Astable multivibrators
- NAND logic



RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges.

CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (T_A = Full Package-Temp. Range)	3	18	V

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V_{DD}) (Voltages referenced to V_{SS} Terminal)	-0.5 to +20 V
INPUT VOLTAGE RANGE, ALL INPUTS	-0.5 to $V_{DD} + 0.5$ V
DC INPUT CURRENT, ANY ONE INPUT	± 10 mA
POWER DISSIPATION PER PACKAGE (P_D):	
For $T_A = -40$ to $+60^\circ\text{C}$ (PACKAGE TYPE E)	500 mW
For $T_A = +60$ to $+85^\circ\text{C}$ (PACKAGE TYPE E)	Derate Linearly at 12 mW/ $^\circ\text{C}$ to 200 mW
For $T_A = -55$ to $+100^\circ\text{C}$ (PACKAGE TYPES D, F, K)	500 mW
For $T_A = +100$ to $+125^\circ\text{C}$ (PACKAGE TYPES D, F, K)	Derate Linearly at 12 mW/ $^\circ\text{C}$ to 200 mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR FOR T_A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types)	100 mW
OPERATING-TEMPERATURE RANGE (T_A):	
PACKAGE TYPES D, F, K, H	-55 to $+125^\circ\text{C}$
PACKAGE TYPE E	-40 to $+85^\circ\text{C}$
STORAGE TEMPERATURE RANGE (T_{stg})	-65 to $+150^\circ\text{C}$
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 $\pm$ 1/32 inch (1.59 $\pm$ 0.79 mm) from case for 10 s max.	$+265^\circ\text{C}$

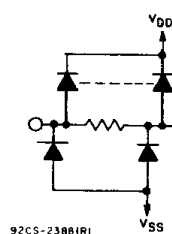
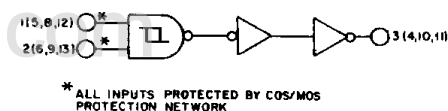


Fig. 1 - Logic diagram-1 of 4 Schmitt triggers.

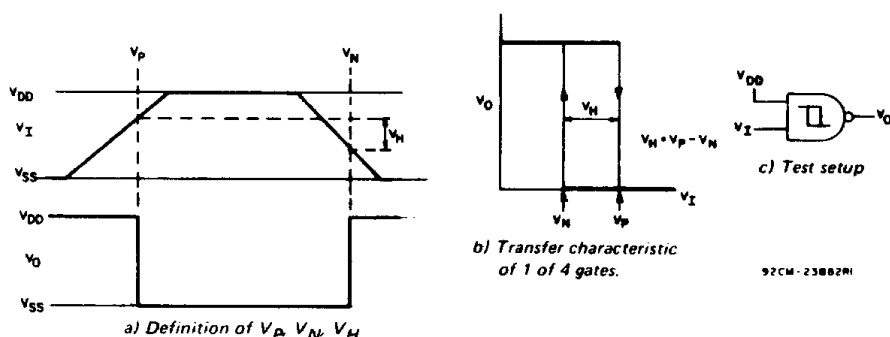


Fig. 2 - Hysteresis definition, characteristic, and test setup.

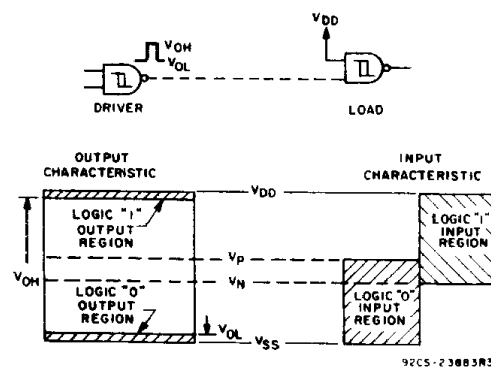


Fig. 3 - Input and output characteristics.

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STATIC ELECTRICAL CHARACTERISTICS

CHARACTER- ISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS	
				Values at -55, +25, +125 Apply to D, F, K, H Packages Values at -40, +25, +85 Apply to E Packages								
	V _O (V)	V _{IN} (V)	V _{DD} (V)	-55	-40	+85	+125	+25				
								MIN.	TYP.	MAX.		
Quiescent Device Current, I _{DD} Max.	—	0,5	5	1	1	30	30	—	0.02	1	μA	
	—	0,10	10	2	2	60	60	—	0.02	2		
	—	0,15	15	4	4	120	120	—	0.02	4		
	—	0,20	20	20	20	600	600	—	0.04	20		
Positive Trigger Threshold Voltage V _P Min.	—	a	5	2.2	2.2	2.2	2.2	2.2	2.9	—	V	
	—	a	10	4.6	4.6	4.6	4.6	4.6	5.9	—		
	—	a	15	6.8	6.8	6.8	6.8	6.8	8.8	—		
	—	b	5	2.6	2.6	2.6	2.6	2.6	3.3	—		
	—	b	10	5.6	5.6	5.6	5.6	5.6	7	—	V	
	—	b	15	6.3	6.3	6.3	6.3	6.3	9.4	—		
	V _P Max.	—	a	5	3.6	3.6	3.6	3.6	—	2.9		3.6
		—	a	10	7.1	7.1	7.1	7.1	—	5.9		7.1
—		a	15	10.8	10.8	10.8	10.8	—	8.8	10.8		
—		b	5	4	4	4	4	—	3.3	4		
—	b	10	8.2	8.2	8.2	8.2	—	7	8.2	V		
—	b	15	12.7	12.7	12.7	12.7	—	9.4	12.7			
Negative Trigger Threshold Voltage V _N Min.	—	a	5	0.9	0.9	0.9	0.9	0.9	1.9	—	V	
	—	a	10	2.5	2.5	2.5	2.5	2.5	3.9	—		
	—	a	15	4	4	4	4	4	5.8	—		
	—	b	5	1.4	1.4	1.4	1.4	1.4	2.3	—		
	—	b	10	3.4	3.4	3.4	3.4	3.4	5.1	—	V	
	—	b	15	4.8	4.8	4.8	4.8	4.8	7.3	—		
	V _N Max.	—	a	5	2.8	2.8	2.8	2.8	—	1.9		2.8
		—	a	10	5.2	5.2	5.2	5.2	—	3.9		5.2
—		a	15	7.4	7.4	7.4	7.4	—	5.8	7.4		
—		b	5	3.2	3.2	3.2	3.2	—	2.3	3.2		
—	b	10	6.6	6.6	6.6	6.6	—	5.1	6.6	V		
—	b	15	9.6	9.6	9.6	9.6	—	7.3	9.6			
Hysteresis Voltage V _H Min.	—	a	5	0.3	0.3	0.3	0.3	0.3	0.9	—	V	
	—	a	10	1.2	1.2	1.2	1.2	1.2	2.3	—		
	—	a	15	1.6	1.6	1.6	1.6	1.6	3.5	—		
	—	b	5	0.3	0.3	0.3	0.3	0.3	0.9	—		
	—	b	10	1.2	1.2	1.2	1.2	1.2	2.3	—	V	
	—	b	15	1.6	1.6	1.6	1.6	1.6	3.5	—		
	V _H Max.	—	a	5	1.6	1.6	1.6	1.6	—	0.9		1.6
		—	a	10	3.4	3.4	3.4	3.4	—	2.3		3.4
—		a	15	5	5	5	5	—	3.5	5		
—		b	5	1.6	1.6	1.6	1.6	—	0.9	1.6		
—	b	10	3.4	3.4	3.4	3.4	—	2.3	3.4	V		
—	b	15	5	5	5	5	—	3.5	5			

^a Input on terminals 1,5,8,12 or 2,6,9,13; other inputs to V_{DD}.

^b Input on terminals 1 and 2, 5 and 6, 8 and 9, or 12 and 13; other inputs to V_{DD}.

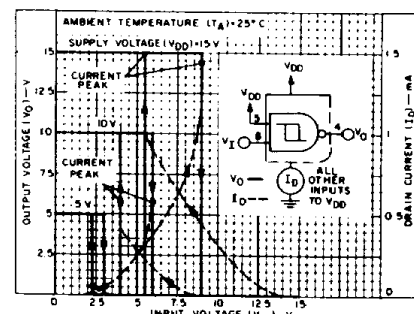


Fig. 4 - Typical current and voltage transfer characteristics.

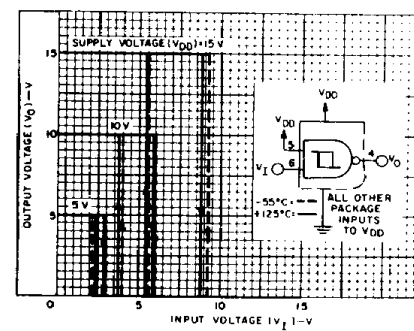


Fig. 5 - Typical voltage transfer characteristics as a function of temperature.

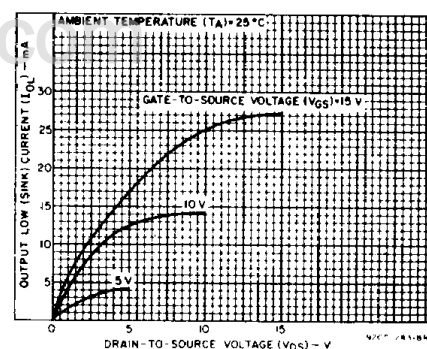


Fig. 6 - Typical output low (sink) current characteristics.

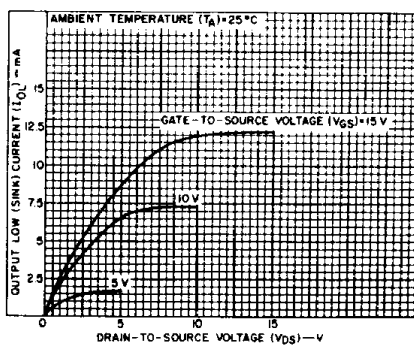


Fig. 7 - Minimum output low (sink) current characteristics.

CD4093B Types

STATIC ELECTRICAL CHARACTERISTICS (CONT'D)

CHARACTER- ISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURE (°C)								UNITS
				Values at -55, +25, +125 Apply to D, F, K, H Packages Values at -40, +25, +85 Apply to E Packages								
	V _O (V)	V _{IN} (V)	V _{DD} (V)	-55	-40	+85	+125	+25				
								MIN.	TYP.	MAX.		
Output Low (Sink) Current, I _{OL} Min.	0.4	0.5	5	0.64	0.61	0.42	0.36	0.51	1	—	mA	
	0.5	0.10	10	1.6	1.5	1.1	0.9	1.3	2.6	—		
	1.5	0.15	15	4.2	4	2.8	2.4	3.4	6.8	—		
Output High (Source) Current, I _{OH} Min.	4.6	0.5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	—	mA	
	2.5	0.5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	—		
	9.5	0.10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	—		
	13.5	0.15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	—		
Output Voltage Low-Level, V _{OL} Max.	—	0.5	5	0.05				—	0	0.05	V	
	—	0.10	10	0.05				—	0	0.05		
	—	0.15	15	0.05				—	0	0.05		
Output Voltage High-Level, V _{OH} Min.	—	0.5	5	4.95				4.95	5	—	V	
	—	0.10	10	9.95				9.95	10	—		
	—	0.15	15	14.95				14.95	—	—		
Input Current, I _{IN} Max.	—	0.18	18	±0.1	±0.1	±1	±1	—	±10 ⁻⁵	±0.1	μA	

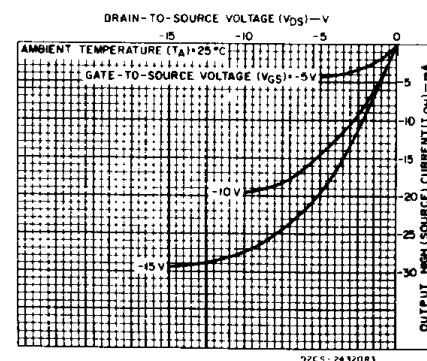


Fig. 8 - Typical output high (source) current characteristics.

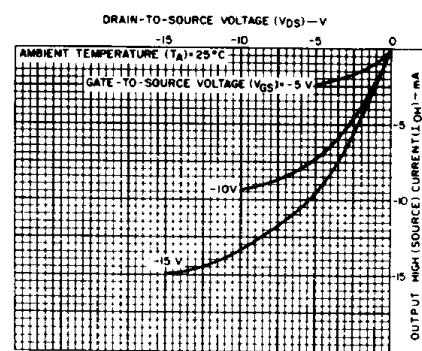


Fig. 9 - Minimum output high (source) current characteristics.

DYNAMIC ELECTRICAL CHARACTERISTICS

At $T_A = 25^\circ\text{C}$; Input $t_r, t_f = 20\text{ ns}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ k}\Omega$

CHARACTERISTIC	TEST CONDITIONS	LIMITS			UNITS
		V _{DD} VOLTS	TYP.	MAX.	
Propagation Delay Time: t _{PHL} , t _{PLH}		5	190	380	ns
		10	90	180	
		15	65	130	
Transition Time, t _{THL} , t _{TLH}		5	100	200	ns
		10	50	100	
		15	40	80	
Input Capacitance, C _{IN}	Any Input		5	7.5	pF

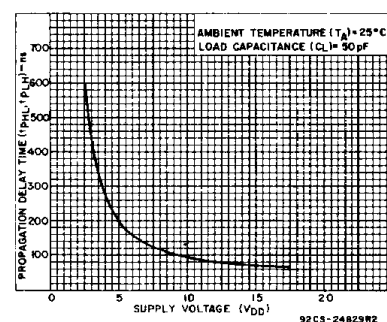


Fig. 10 - Typical propagation delay time vs. supply voltage.

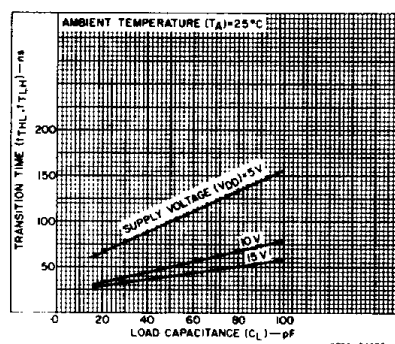


Fig. 11 - Typical transition time vs. load capacitance.

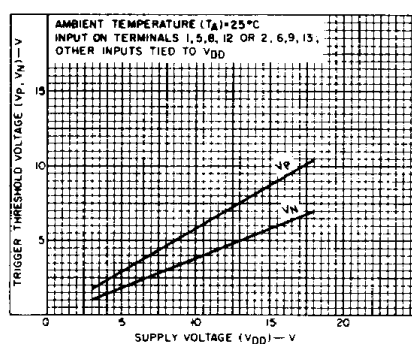


Fig. 12 - Typical trigger threshold voltage vs. V_{DD}

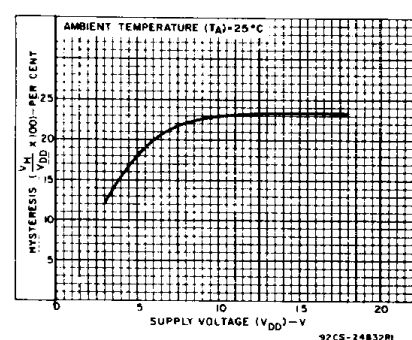


Fig. 13 - Typical per cent hysteresis vs. supply voltage.

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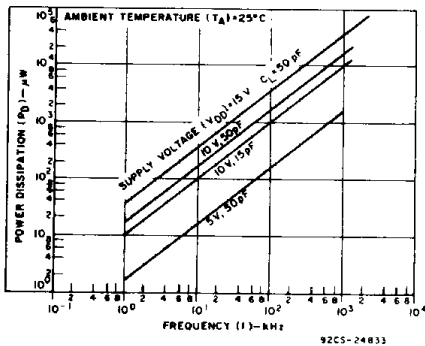


Fig. 14 - Typical power dissipation vs. frequency characteristics.

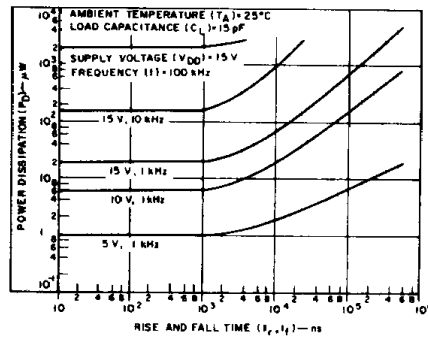


Fig. 15 - Typical power dissipation vs. rise and fall times.

APPLICATIONS

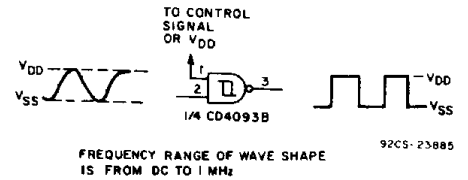


Fig. 16 - Wave shaper.

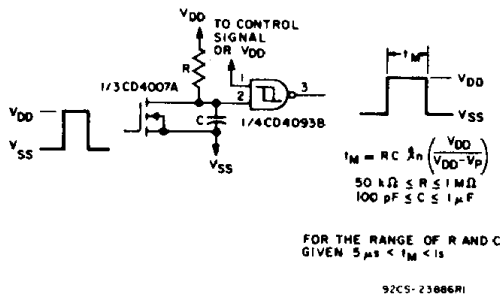


Fig. 17 - Monostable multivibrator.

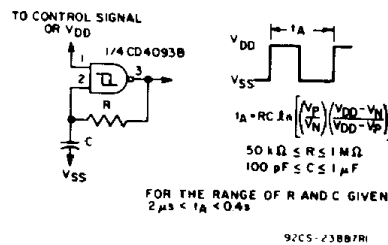


Fig. 18 - Astable multivibrator.

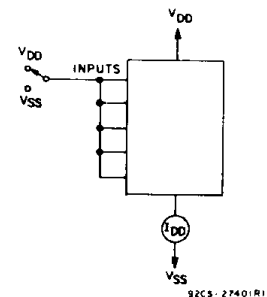


Fig. 19 - Quiescent device current test circuit.

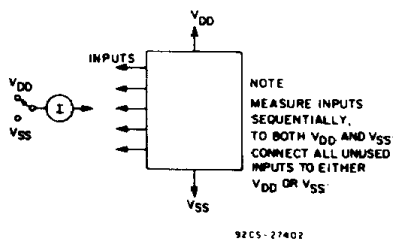
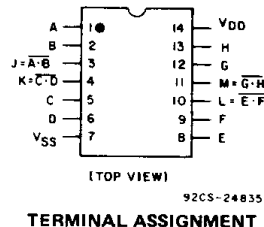
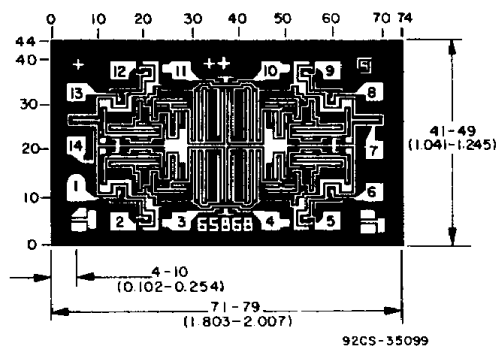


Fig. 20 - Input current test circuit.



Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).



Dimensions and Pad Layout for CD4093BH

The photographs and dimensions of each CMOS chip represent a chip when it is part of the wafer. When the wafer is separated into individual chips, the angle of cleavage may vary with respect to the chip face for different chips. The actual dimensions of the isolated chip, therefore, may differ slightly from the nominal dimensions shown. The user should consider a tolerance of ± 3 mils to ± 16 mils applicable to the nominal dimensions shown.